GLBCX53 PNP SILICON EPITAXIAL TRANSISTOR

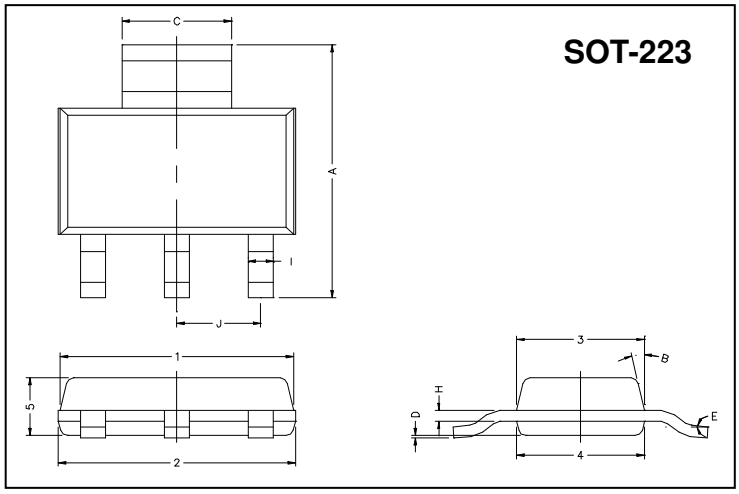
Description

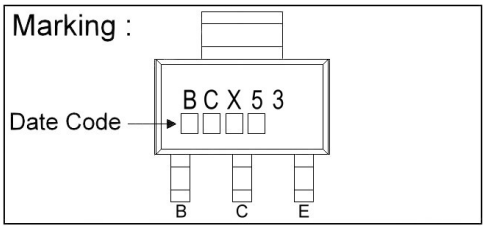
The GLBCX53 is designed for use in driver stages of audio amplifiers and medium power general purpose amplification.

Features

- Collector-Emitter Voltage: V_{CEO}=-80V
- Complementary to GLBCP56

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-65 ~ +150	℃
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collect Current(DC)	I_C	1	A
Total Power Dissipation	P_D	1.5	W

Electrical Characteristics (Ta = 25℃)

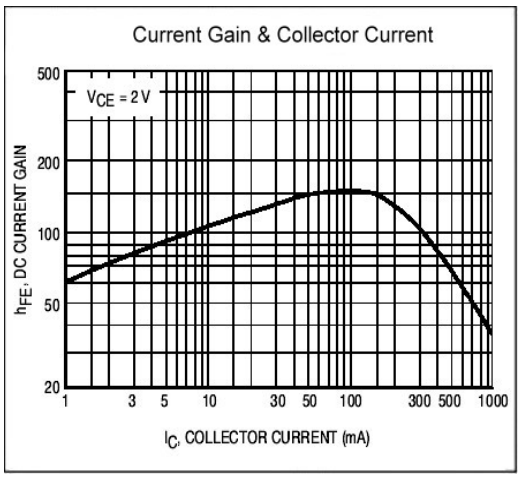
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-100	-	-	V	I_C=-100uA, I_E=0
BV_{CEO}	-80	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-10uA, I_C=0
I_{CBO}	-	-	-100	nA	V_{CB}=-30V, I_E=0
I_{EBO}	-	-	-100	nA	V_{EB}=-5V, I_C=0
*$V_{CE(sat)1}$	-	-	-500	mV	I_C=-500mA, I_B=-50mA
*$V_{BE(on)}$	-	-	-1000	mV	I_C=-500mA, V_{CE}=-2V,
*h_{FE1}	63	-	-		V_{CE}=-2V, I_C=-5mA
*h_{FE2}	63	-	250		V_{CE}=-2V, I_C=-150mA
*h_{FE3}	40	-	-		V_{CE}=-2V, I_C=-500mA
fT	100	-	-	MHz	V_{CE}=-5V, I_C=-10mA, f=100MHz

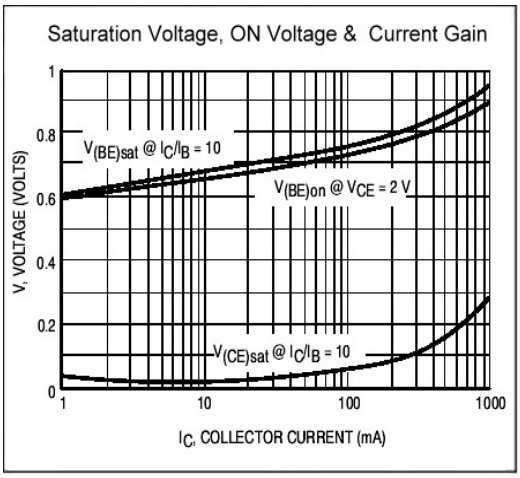
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

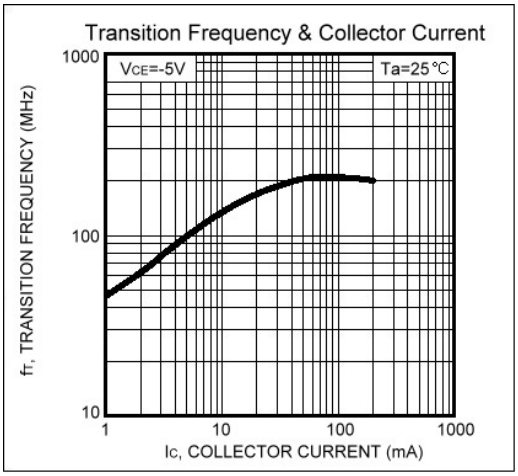
Classification Of h_{FE2}

Rank	A	B
Range	63 - 160	100 - 250

Characteristics Curve







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